

Spec. No. : C175FP Issued Date : 2015.05.13

Revised Date : Page No. : 1/5

20Amp. MOS BARRIER RECTIFIER

SKM2045CTFP

IF(AV)	2 x 10A
Vrrm	45V
VF	0.52V
Tj	150°C

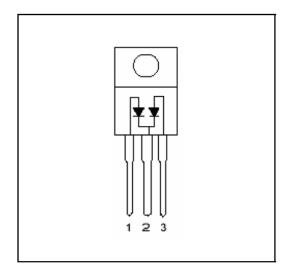
Features

- 150°C operating junction temperature
- Softest, fast switching capability
- Reduced ultra-low forward voltage drop (VF); better efficiency and cooler operation.
- Lead-Free Finish; RoHS Compliant
- Halogen and Antimony Free. "Green" Device
- MCD technology provides a superior avalanche capability than schottky diodes

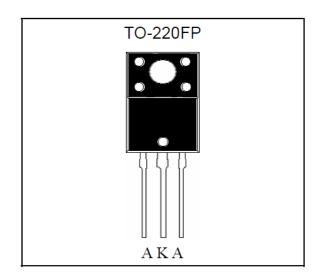
Mechanical Data

- Case: TO-220FP molded plastic
- Weight: 2.2 grams approximately
- Terminals: Pure tin plated, lead-free, solderable per MIL-STD-750 method 2026
- Epoxy: UL 94V-0 rate flame retardant
- Polarity: As marked.

Equivalent Circuit



Outline





Spec. No. : C175FP Issued Date : 2015.05.13

Revised Date : Page No. : 2/5

Maximum Ratings and Electrical Characteristics

(Rating at 25°C ambient temperature unless otherwise specified. Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.)

Parameter			Symbol	Min.	Тур.	Max.	Units
Maximum DC blocking voltage		V _{DC}			45	V	
Maximum Recurrent peak reverse voltage		Vrrm			45	V	
Maximum RMS voltage			V _{RMS}			32	V
Maximum instantaneous forward voltage	ge at	Tc=25°C	V_{F}		0.52	0.56	
IF=10A per diode		Tc=125°C	V F		0.5		V
Daviana aumant man diada	$V_R=4$	45 V, Tc=25°C	In		60	300	μΑ
Reverse current per diode	$V_R=4$	45 V, Tc=125°C	IR		15	35	mA
Maximum Average forward rectified current per device		IF(AV)			20	A	
Maximum Average forward rectified current per diode		IF(AV)			10	A	
Non-repetitive peak forward surge current @							
8.3ms single half sine wave superimposed on		Ifsm			120	Α	
rated load (JEDEC method) per diode							
Peak Repetitive Reverse Surge Current (2uS-1Khz)			Irrm			2	A
Isolation voltage			VAC	1500			V
Maximum Rate of Voltage Change (at Rated VR)		dv/dt			10000	V/uS	
Storage temperature range			Tstg	-55		150	$^{\circ}$ C
Operating junction temperature range		TJ	-55		150	$^{\circ}\mathbb{C}$	

Thermal Data

Parameter	Symbol	Value	Unit
Typical Thermal Resistance, Junction-to-case	Rth,j-c	7	°C/W

Ordering Information

Device	Package	Shipping		
SKM2045CTFP-0-UB-S	TO-220FP (Pb-free lead plating)	50 pcs/tube, 20tubes/box, 4boxes/carton		
	Environment friendly grade: S for RoHS of compliant and green compound products Packing spec, UB: 50 pcs / tube, 20 tubes/ Product rank, zero for no rank products Product name	•		



Spec. No. : C175FP Issued Date : 2015.05.13

Revised Date : Page No. : 3/5

Typical Characteristics

Forward Current Derating Curve

12

(V) 10

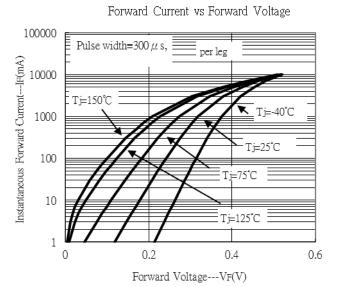
per leg

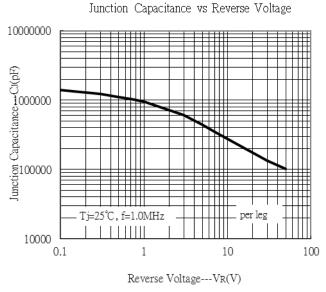
per leg

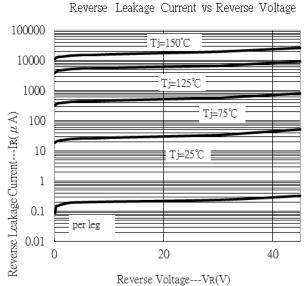
resistive or inductive load

0 25 50 75 100 125 150 175 200

Case Temperature---TC($^{\circ}$ C)









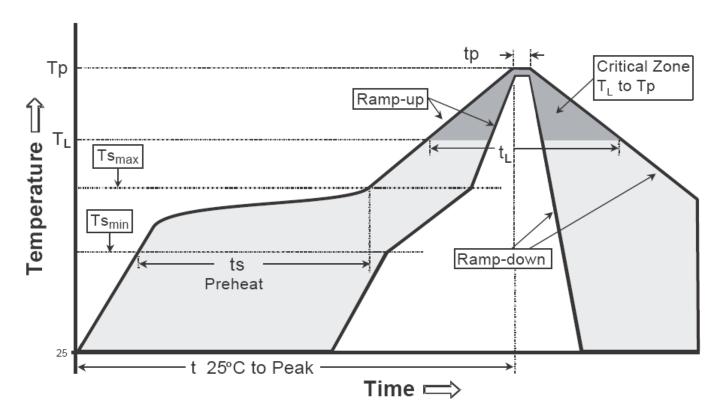
Spec. No. : C175FP Issued Date : 2015.05.13

Revised Date : Page No. : 4/5

Recommended wave soldering condition

Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

Recommended temperature profile for IR reflow



Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly		
Average ramp-up rate (Tsmax to Tp)	3°C/second max.	3°C/second max.		
Preheat				
-Temperature Min(Ts min)	100°C	150°C		
-Temperature Max(Ts max)	150°C	200°C		
-Time(ts min to ts max)	60-120 seconds	60-180 seconds		
Time maintained above:				
-Temperature (T∟)	183°C	217°C		
- Time (t∟)	60-150 seconds	60-150 seconds		
Peak Temperature(T _P)	240 +0/-5 °C	260 +0/-5 °C		
Time within 5°C of actual peak temperature(tp)	10-30 seconds	20-40 seconds		
Ramp down rate	6°C/second max.	6°C/second max.		
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.		

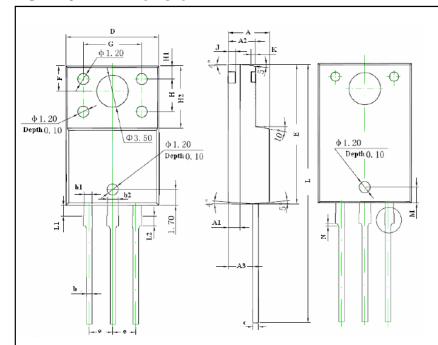
Note: All temperatures refer to topside of the package, measured on the package body surface.

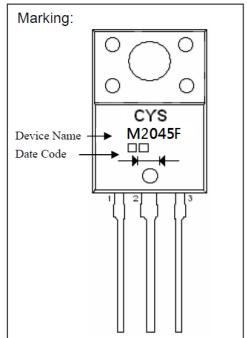


Spec. No. : C175FP Issued Date : 2015.05.13

Revised Date : Page No. : 5/5

TO-220FP Dimension





3-Lead TO-220FP Plastic Package CYStek Package Code: FP

Style: Pin 1.Anode 2.Cathode 3.Anode

*Typical

DIM	Inc	hes	Millim	eters	DIM	Inches		Millimeters	
DIIVI	Min.	Max.	Min.	Max.	DIIVI	Min.	Max.	Min.	Max.
Α	0.171	0.183	4.35	4.65	G	0.246	0.258	6.25	6.55
A1	0.051 REF		1.300 REF		Н	0.138	REF	3.50	REF
A2	0.112	0.124	2.85	3.15	H1	0.055	REF	1.40	REF
А3	0.102	0.110	2.60	2.80	H2	0.256	0.272	6.50	6.90
b	0.020	0.030	0.50	0.75	J	0.031	REF	0.80	REF
b1	0.031	0.041	0.80	1.05	K	0.0	0.020 0.50 F		REF
b2	0.047	REF	1.20 REF		L	1.102	1.118	28.00	28.40
С	0.020	0.030	0.500	0.750	L1	0.043	0.051	1.10	1.30
D	0.396	0.404	10.06	10.26	L2	0.036	0.043	0.92	1.08
E	0.583	0.598	14.80	15.20	М	0.067	REF	1.70	REF
е	0.100 *		2.54*		N	0.012	REF	0.30	REF
F	0.106	REF	2.70	REF					

Notes: 1.Controlling dimension: millimeters.

- 2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.
- 3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

Material:

- Lead: Pure tin plated.
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0.

Important Notice:

- All rights are reserved. Reproduction in whole or in part is prohibited without the prior written approval of CYStek.
- CYStek reserves the right to make changes to its products without notice.
- CYStek semiconductor products are not warranted to be suitable for use in Life-Support Applications, or systems.
- CYStek assumes no liability for any consequence of customer product design, infringement of patents, or application assistance.